



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
40V	4.3mΩ @ V _{GS} = 10V	96A
	7.5mΩ @ V _{GS} = 4.5V	73A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Backlighting
- Power-management functions
- DC-DC converters

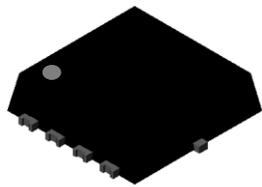
Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Low R_{DS(ON)} – Ensures On-State Losses are Minimized
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Wettable Flank for Improved Optical Inspection
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application

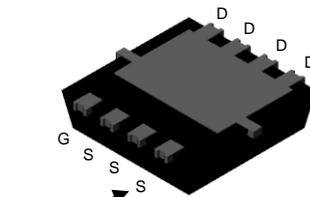
Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)

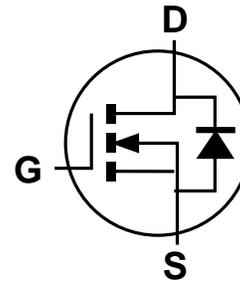
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



Equivalent Circuit

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	40	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 5), $V_{GS} = 10\text{V}$	I_D	$T_C = +25^\circ\text{C}$	96
		$T_C = +100^\circ\text{C}$	68
Continuous Drain Current (Note 6), $V_{GS} = 10\text{V}$	I_D	$T_A = +25^\circ\text{C}$	23
		$T_A = +100^\circ\text{C}$	16
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	384	A
Maximum Continuous Body Diode Forward Current (Note 5)	I_S	96	A
Pulsed Body Diode Forward Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	384	A
Avalanche Current, $L = 1\text{mH}$	I_{AS}	12.9	A
Avalanche Energy, $L = 1\text{mH}$	E_{AS}	83.2	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_D	3.6	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	41	$^\circ\text{C/W}$
Total Power Dissipation (Note 5)	P_D	65	W
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	2.3	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

Notes: 5. Thermal resistance from junction to soldering point (on the exposed drain pad).
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.4	4.3	mΩ	V _{GS} = 10V, I _D = 20A
		—	5.4	7.5		V _{GS} = 4.5V, I _D = 15A
Diode Forward Voltage	V _{SD}	—	0.8	1.0	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2737	—	pF	V _{DS} = 20V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	835	—		
Reverse Transfer Capacitance	C _{rss}	—	67	—		
Gate Resistance	R _g	—	2.4	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	36.9	—	nC	V _{DS} = 20V, I _D = 20A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	16.9	—		
Gate-Source Charge	Q _{gs}	—	8.6	—		
Gate-Drain Charge	Q _{gd}	—	3.6	—		
Turn-On Delay Time	t _{D(ON)}	—	7.1	—	ns	V _{DD} = 20V, V _{GS} = 10V R _g = 1.6Ω, I _D = 20A
Turn-On Rise Time	t _r	—	10.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	31.0	—		
Turn-Off Fall Time	t _f	—	13.0	—		
Body Diode Reverse Recovery Time	t _{RR}	—	36.0	—	ns	I _F = 15A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	36.0	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

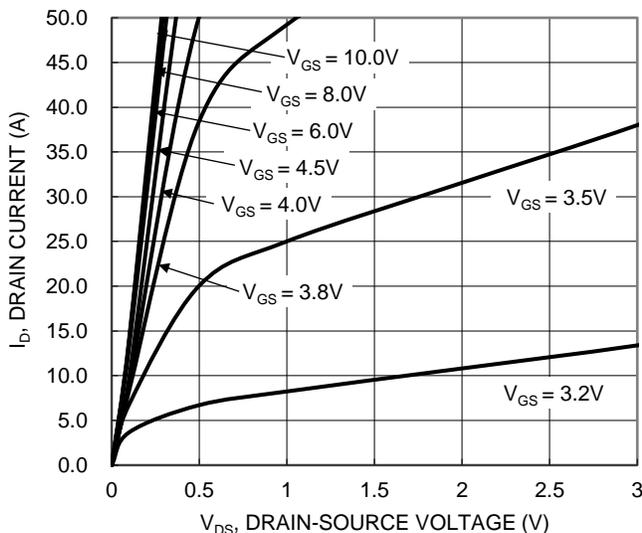


Figure 1. Typical Output Characteristic

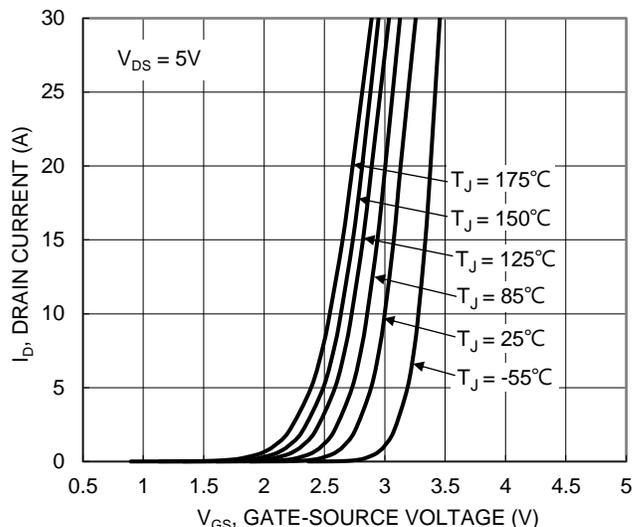


Figure 2. Typical Transfer Characteristic

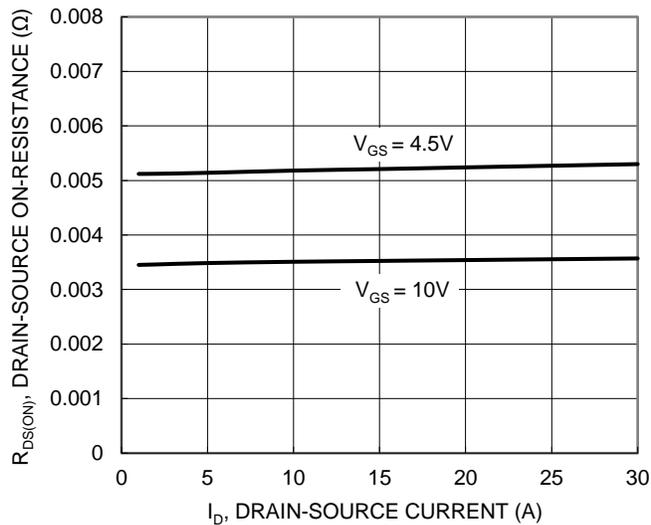


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

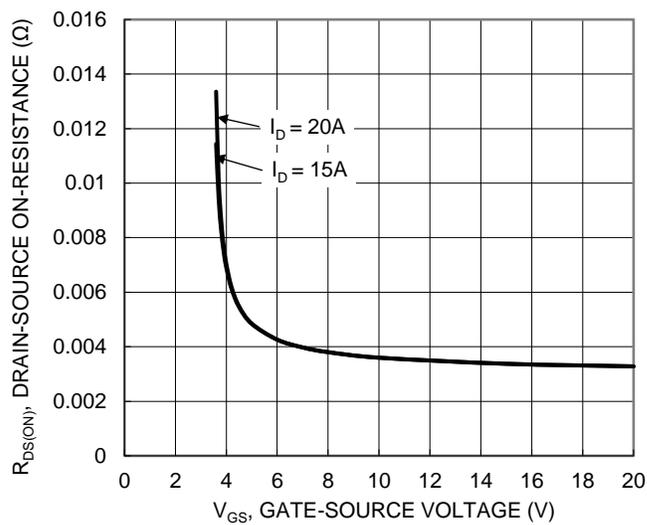


Figure 4. Typical Transfer Characteristic

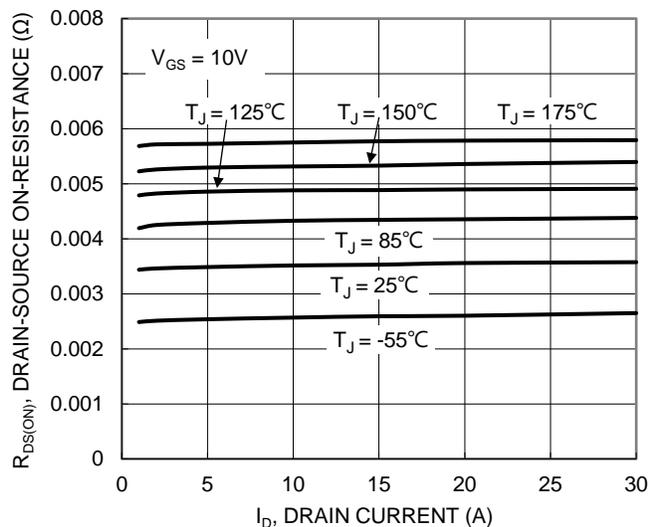


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

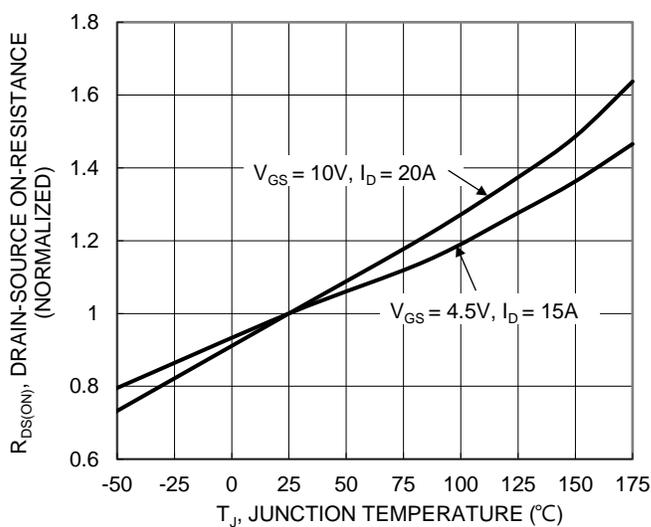


Figure 6. On-Resistance Variation with Junction Temperature

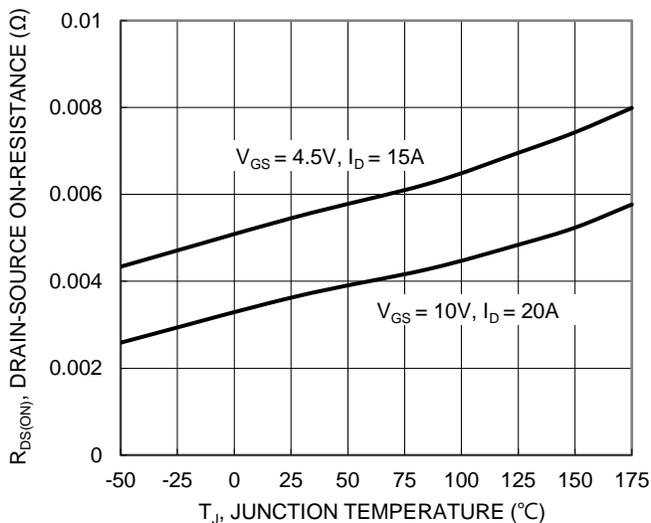


Figure 7. On-Resistance Variation with Junction Temperature

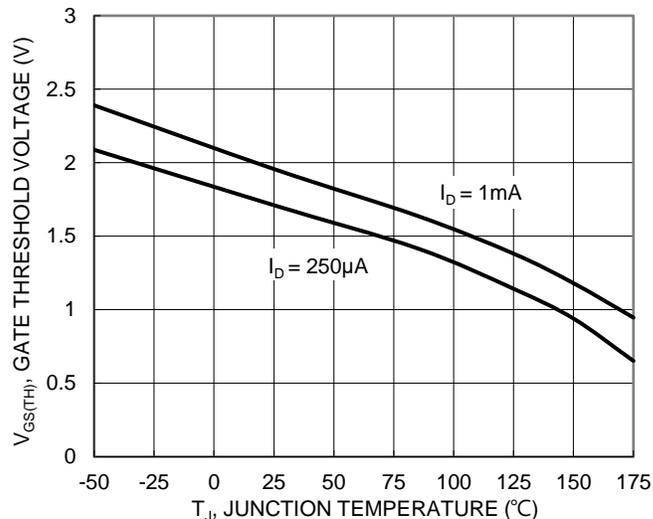


Figure 8. Gate Threshold Variation vs. Junction Temperature

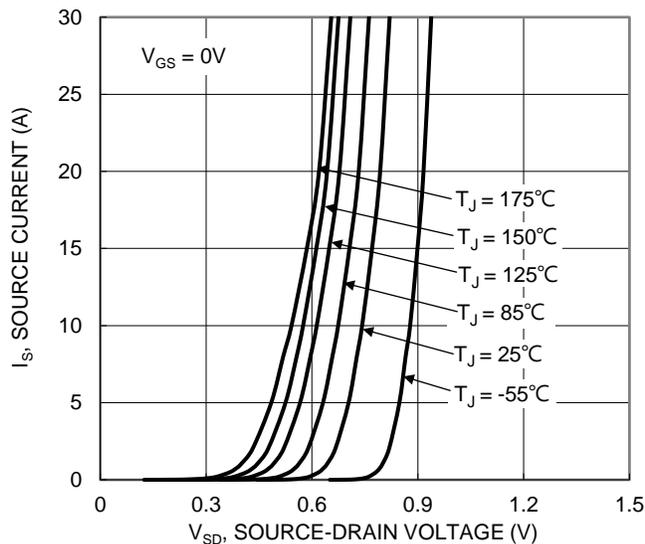


Figure 9. Diode Forward Voltage vs. Current

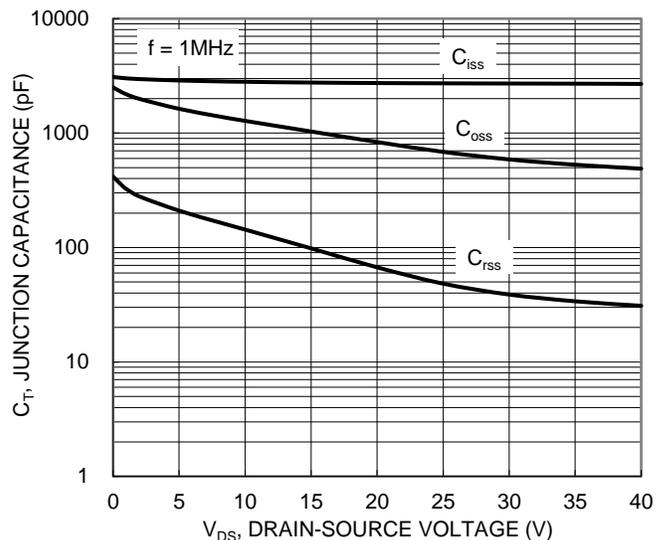


Figure 10. Typical Junction Capacitance

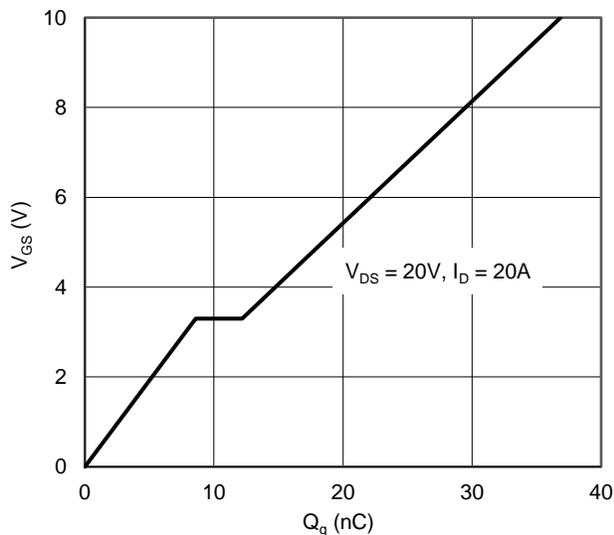


Figure 11. Gate Charge

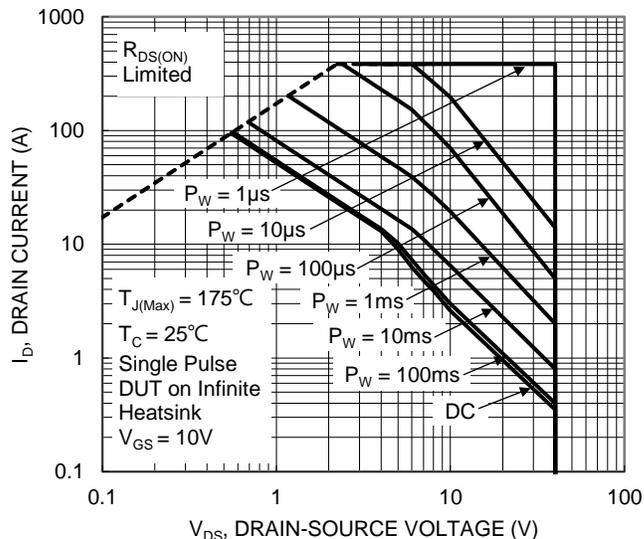


Figure 12. SOA, Safe Operation Area

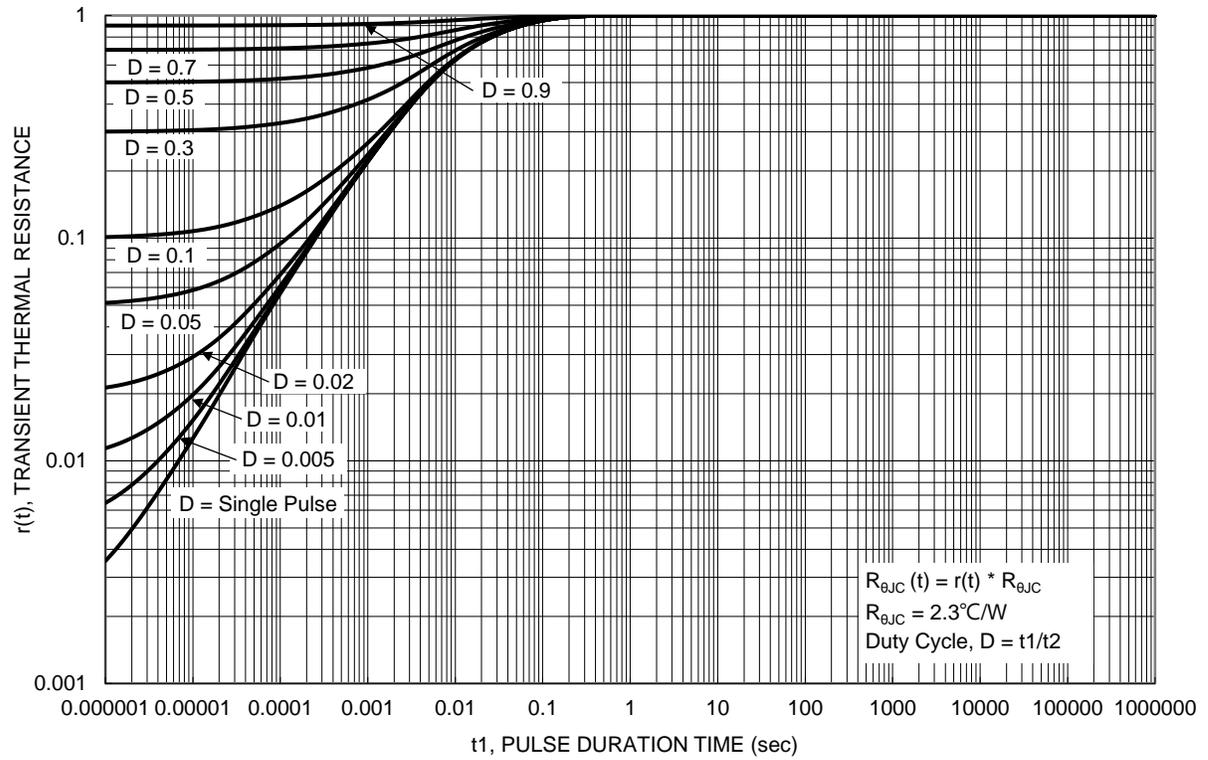
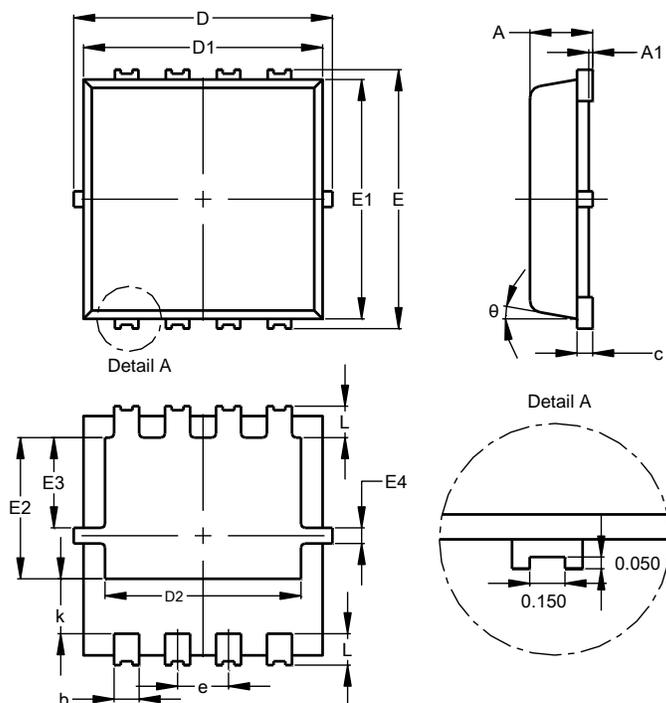


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

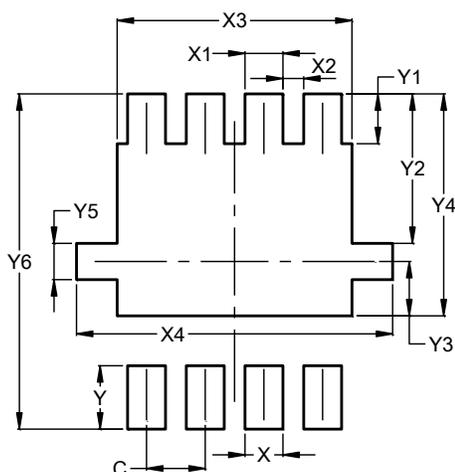
PowerDI3333-8 (SWP) (Type UX)



PowerDI3333-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
theta	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700